



### P-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

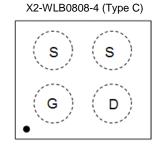
BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> T <sub>A</sub> = +25°C
-12V	$50m\Omega$ @ $V_{GS} = -4.5V$	-4.8A
	$65m\Omega @ V_{GS} = -2.5V$	-4.2A

## **Description**

This new generation MOSFET has been designed to minimize the onstate resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications. It is a high performance MOSFET in ultra-small 0.8mm x0.8mm package.

## **Applications**

- Portable Applications
- Load Switch
- **Power Management Functions**



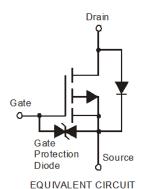
Top View

**Features and Benefits** 

- Ultra Small 0.8mm x 0.8mm Package
- Built-in G-S Protection Diode Against ESD
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

## **Mechanical Data**

- Case: X2-WLB0808-4
- Terminal Connections: See Diagram Below
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish —SnAgCu. Solderable per MIL-STD-202 Method 208 @1)
- Weight: 0.0011 grams (Approximate)



Ordering Information (Note 4)

Part Number	Case	Packaging
DMP1045UCB4-7	X2-WLB0808-4 (Type C)	3000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

# **Marking Information**



9M = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: G = 2019) M or  $\overline{M}$  = Month (ex: 9 = September)

### Date Code Key

Year	2019	2020	2021	2022	2023	2024	2025
Code	G	Н		J	K	L	M

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V <sub>DSS</sub>	-12	V		
Gate-Source Voltage		$V_{GSS}$	±8	V	
Continuous Drain Current (Note 7) V <sub>GS</sub> = -4.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	-2.6 -2.1	А
Continuous Drain Current (Note 5) V <sub>GS</sub> = -4.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	-4.8 -3.8	А

## **Thermal Characteristics**

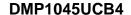
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 7)	P <sub>D</sub>	0.53	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 7)	R <sub>θJA</sub>	238	°C/W
Power Dissipation (Note 5)	P <sub>D</sub>	1.75	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5)	R <sub>0JA</sub>	71	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

## Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

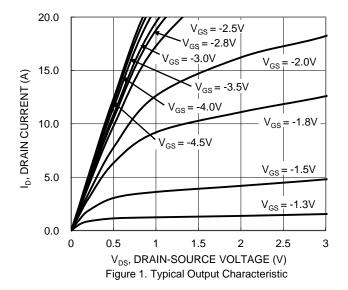
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)	•					
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-12	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	_	_	-1	μΑ	V <sub>DS</sub> = -9.6V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±10	μΑ	$V_{GS} = \pm 8V$ , $V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.3	-0.67	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
		_	42	50		$V_{GS} = -4.5V, I_D = -2A$
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	51	65	mΩ	V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -2A
		_	67	100		V <sub>GS</sub> = -1.8V, I <sub>D</sub> = -1A
Diode Forward Voltage	V <sub>SD</sub>		-0.7	-1.2	V	$V_{GS} = 0V, I_S = -1.5A$
DYNAMIC CHARACTERISTICS (Note 9)	1		•		•	
Input Capacitance	C <sub>iss</sub>	_	535	_		
Output Capacitance	Coss	_	136	_	pF	$V_{DS} = -6V, V_{GS} = 0V,$ f = 1.0MHz
Reverse Transfer Capacitance	C <sub>rss</sub>	_	70	_		I = 1.0IVII IZ
Total Gate Charge	Qg		6.1	_		4.57.77
Gate-Source Charge	Qgs		0.4	_	nC	$V_{GS} = -4.5V, V_{DD} = -6V,$
Gate-Drain Charge	$Q_{gd}$		2.0	_		$I_D = -2A$
Turn-On Delay Time	t <sub>D(ON)</sub>		28.8	-		
Turn-On Rise Time	t <sub>R</sub>		11.3	_		$V_{DD} = -6V, I_{D} = -2A$
Turn-Off Delay Time	t <sub>D(OFF)</sub>	-	115.0	_	ns	$V_{GEN} = -4.5V$ , $R_g = 3\Omega$
Turn-Off Fall Time	t <sub>F</sub>	_	44.6	_	1	

Notes:

- 5. Device mounted on FR-4 material with 1-inch<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz. (0.071-mm thick) Cu.
- 6. Repetitive rating, pulse width limited by junction temperature.
- 7. Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to production testing.







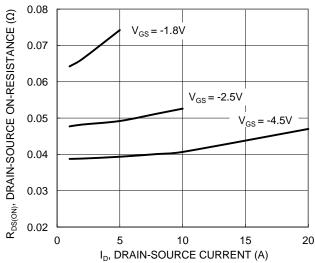


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

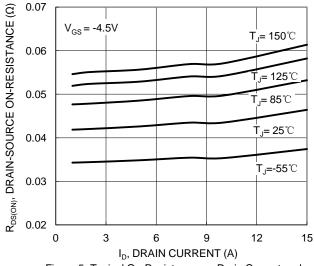
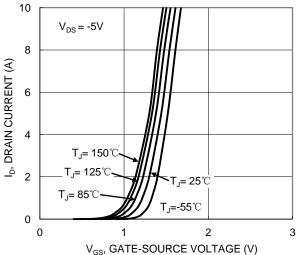
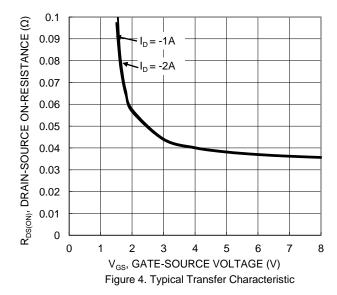


Figure 5. Typical On-Resistance vs. Drain Current and Temperature



V<sub>GS</sub>, GATE-SOURCE VOLTAGE (V)
Figure 2. Typical Transfer Characteristic



1.6 R<sub>DS(ON)</sub>, DRAIN-SOURCE ON-RESISTANCE  $V_{GS} = -4.5V, I_{D} = -2A$ 1.4  $V_{GS} = -2.5V, I_{D}$ (NORMALIZED) 1.2  $V_{GS} = -1.8V, I_{D} = -1A$ 8.0 0.6 -50 -25 25 50 75 100 125 150 175  $T_J$ , JUNCTION TEMPERATURE (°C)

Figure 6. On-Resistance Variation with Temperature



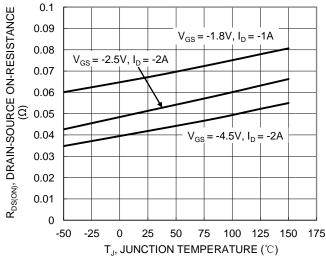


Figure 7. On-Resistance Variation with Temperature

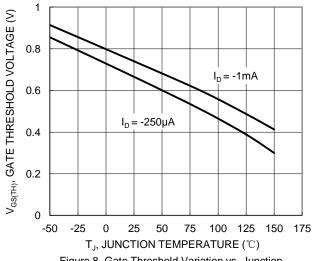


Figure 8. Gate Threshold Variation vs. Junction Temperature

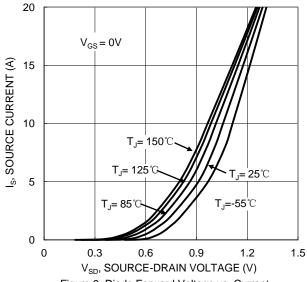
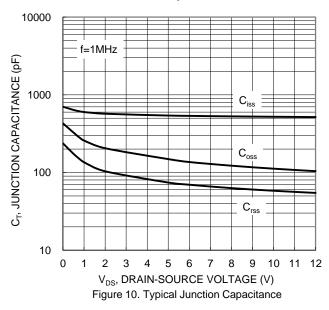
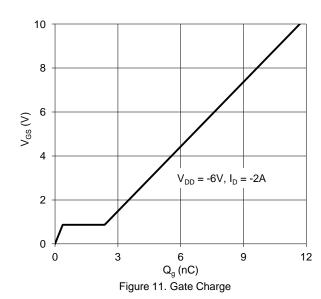


Figure 9. Diode Forward Voltage vs. Current



100 R<sub>DS(ON)</sub> Limited =100µs 10 ID, DRAIN CURRENT (A) =10ms 0.1 T<sub>C</sub> = 25°C Single Pulse DUT on 1\*MRP board  $V_{GS} = -10V$ 0.01 0.1 10 100 V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area





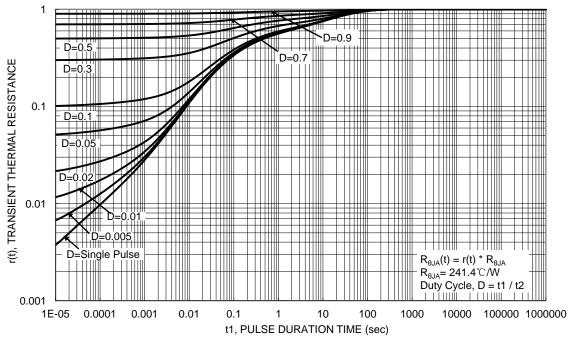


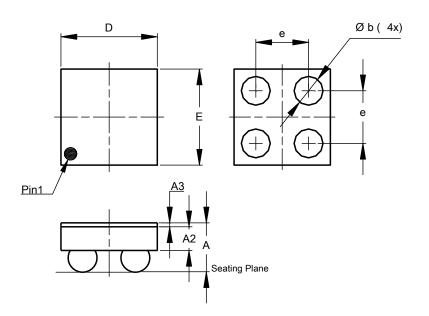
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

## X2-WLB0808-4 (Type C)

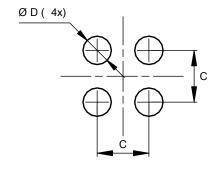


X2-WLB0808-4									
	(Type C)								
Dim	Dim Min Max Typ								
Α		0.4000	0.3750						
A2			0.1800						
A3	0.0200	0.0300	0.0250						
b	0.1971	0.2409	0.2190						
D	0.7400	0.8000	0.7700						
Е	0.7400	0.8000	0.7700						
е			0.4000						
All Dimensions in mm									

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

## X2-WLB0808-4 (Type C)



Dimensions	Value (in mm)		
С	0.400		
D	0.219		



#### IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

#### LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
  - 1. are intended to implant into the body, or
  - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2019, Diodes Incorporated

www.diodes.com